

**METHOD OF FORMING AN UNDERLAYER OF A BI-LAYER RESIST
FILM AND METHOD OF FABRICATING A SEMICONDUCTOR DEVICE
USING THE SAME**

5

ABSTRACT OF THE DISCLOSURE

A method of forming an underlayer of a bi-layer resist including forming a blended material by blending a polymer having an aromatic group and a methacrylate polymer, and coating a substrate with the blended material. The blended material coated on the substrate is irradiated to form an underlayer.

10

The polymer having the aromatic group may be a novolac polymer or a naphthalene polymer.